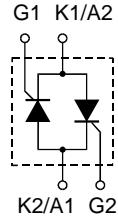


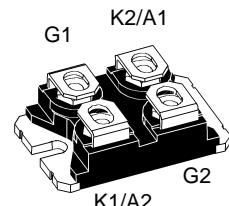
AC Controller Modules

I_{RMS} = 54 A
V_{RRM} = 1200-1600 V

V _{RSM} V _{DSM} V	V _{RRM} V _{DRM} V	Type
1200	1200	MMO 62-12io6
1600	1600	MMO 62-16io6



miniBLOC, SOT-227 B



Symbol	Test Conditions	Maximum Ratings		
I _{RMS}	T _C = 110°C, 50 - 400 Hz, module	54	A	
I _{TRMS}	T _{VJ} = T _{VJM}	39	A	
I _{TAVM}	T _C = 110°C; (180° sine)	25	A	
I _{TSM}	T _{VJ} = 45°C; V _R = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	400 430	A A
	T _{VJ} = T _{VJM} V _R = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	350 370	A A
I ² t	T _{VJ} = 45°C V _R = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	800 780	A ² s A ² s
	T _{VJ} = T _{VJM} V _R = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	610 570	A ² s A ² s
(di/dt) _{cr}	T _{VJ} = T _{VJM} f = 50 Hz, t _p = 200 μs V _D = 2/3 V _{DRM} I _G = 0.3 A di _G /dt = 0.3 A/μs	repetitive, I _T = 150 A non repetitive, I _T = I _{TAVM}	100 500	A/μs A/μs
(dv/dt) _{cr}	T _{VJ} = T _{VJM} ; R _{GK} = ∞; method 1 (linear voltage rise)	V _{DR} = 2/3 V _{DRM}	1000	V/μs
P _{GM}	T _{VJ} = T _{VJM} I _T = I _{TAVM}	t _p = 30 μs t _p = 300 μs	10 5	W W
P _{GAVM}			0.5	W
V _{RGM}			10	V
T _{VJ}			-40...+150	°C
T _{VJM}			150	°C
T _{stg}			-40...+150	°C
V _{ISOL}	50/60 Hz, RMS I _{ISOL} ≤ 1 mA		2500	V~
M _d	Mounting torque (M4) Terminal connection torque (M4)		1.1 - 1.5 / 9 - 13	Nm/lb.in.
Weight	typ.	30	g	

Data according to IEC 60747 and to a single thyristor/diode unless otherwise stated.
 IXYS reserves the right to change limits, test conditions and dimensions.

Symbol	Test Conditions	Characteristic Values		
I_R, I_D	$T_{VJ} = T_{VJM}$; $V_R = V_{RRM}$; $V_D = V_{DRM}$	≤	12	mA
V_T	$I_T = 45 \text{ A}$; $T_{VJ} = 25^\circ\text{C}$	≤	1.57	V
V_{TO}	For power-loss calculations only	0.85		V
r_T		12		$\text{m}\Omega$
V_{GT}	$V_D = 6 \text{ V}$; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$	≤	1.5	V
I_{GT}	$V_D = 6 \text{ V}$; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$	≤	100	mA
V_{GD}	$T_{VJ} = T_{VJM}$;	$V_D = 2/3 V_{DRM}$	≤	0.2 V
I_{GD}		≤	5	mA
I_L	$T_{VJ} = 25^\circ\text{C}$; $t_p = 10 \mu\text{s}$ $I_G = 0.3 \text{ A}$; $di_G/dt = 0.3 \text{ A}/\mu\text{s}$	≤	250	mA
I_H	$T_{VJ} = 25^\circ\text{C}$; $V_D = 6 \text{ V}$; $R_{GK} = \infty$	≤	100	mA
t_{gd}	$T_{VJ} = 25^\circ\text{C}$; $V_D = 1/2 V_{DRM}$ $I_G = 0.3 \text{ A}$; $di_G/dt = 0.3 \text{ A}/\mu\text{s}$	≤	2	μs
t_q	$T_{VJ} = T_{VJM}$; $I_T = 20 \text{ A}$, $t_p = 200 \mu\text{s}$; $di/dt = -10 \text{ A}/\mu\text{s}$ $V_R = 100 \text{ V}$; $dv/dt = 15 \text{ V}/\mu\text{s}$; $V_D = 2/3 V_{DRM}$	typ.	150	μs
R_{thJC}	per thyristor; DC current		0.91	K/W
	per module		0.455	K/W
R_{thCH}	per thyristor; DC current	typ.	0.1	K/W
	per module	typ.	0.05	K/W
d_s	Creeping distance on surface		8	mm
d_a	Creepage distance in air		4	mm
a	Max. allowable acceleration		50	m/s^2

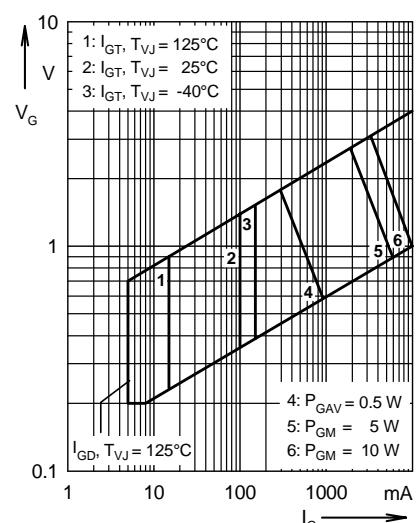


Fig. 1 Gate trigger characteristics

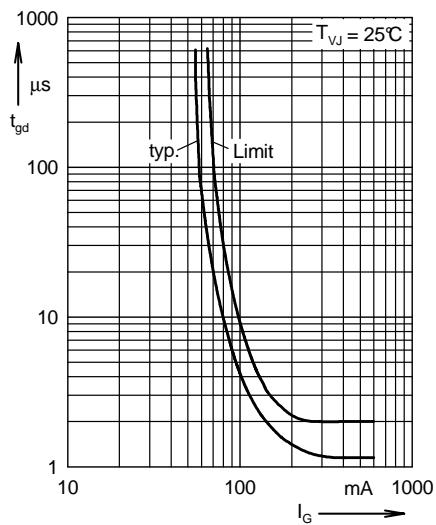
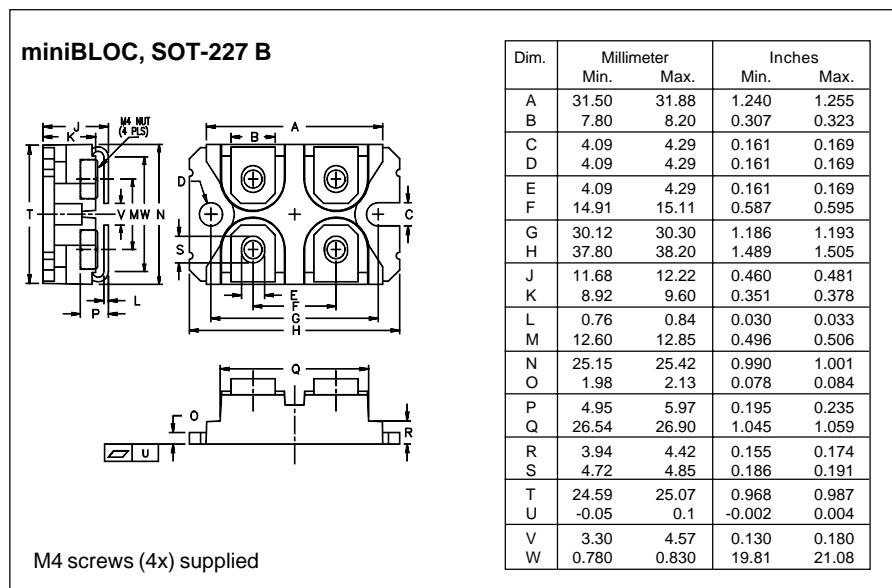


Fig. 2 Gate trigger delay time



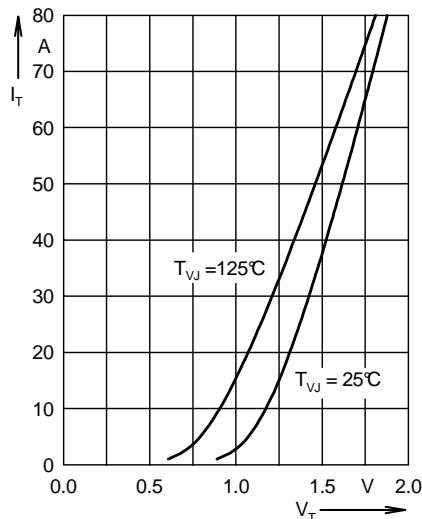


Fig. 3 Forward current versus voltage drop per leg

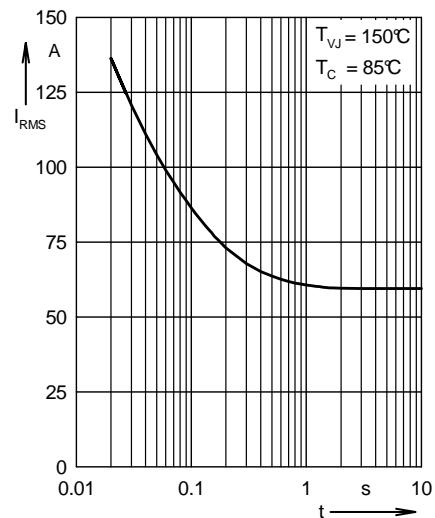


Fig. 4 Rated RMS current versus time (360° conduction)

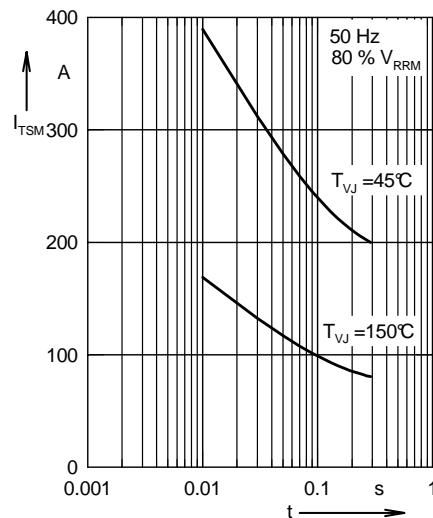


Fig. 5 Surge overload current

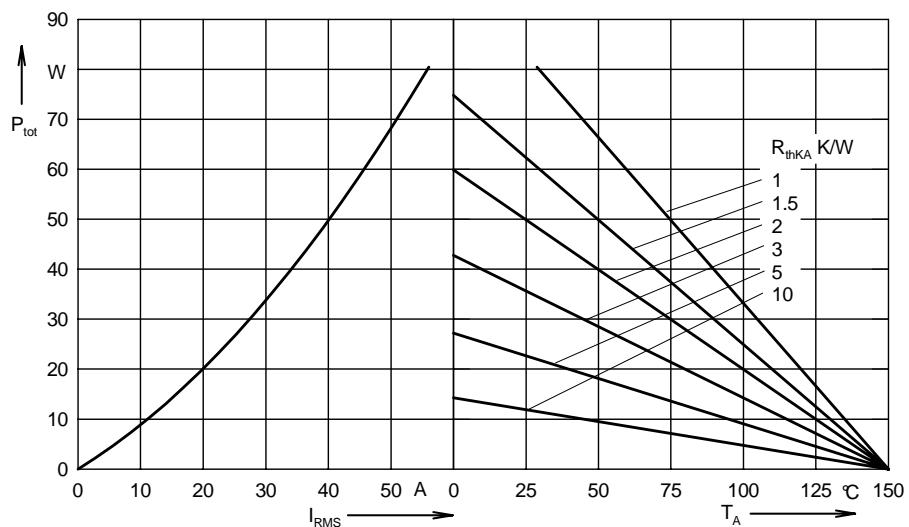


Fig. 6 Load current capability for single AC controller; 1 x MMO62

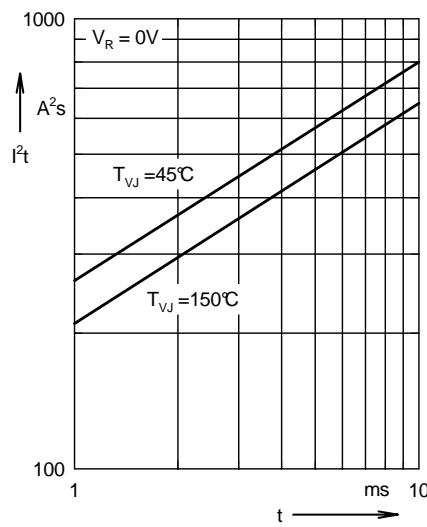


Fig. 7 I^2t versus time (per thyristor)

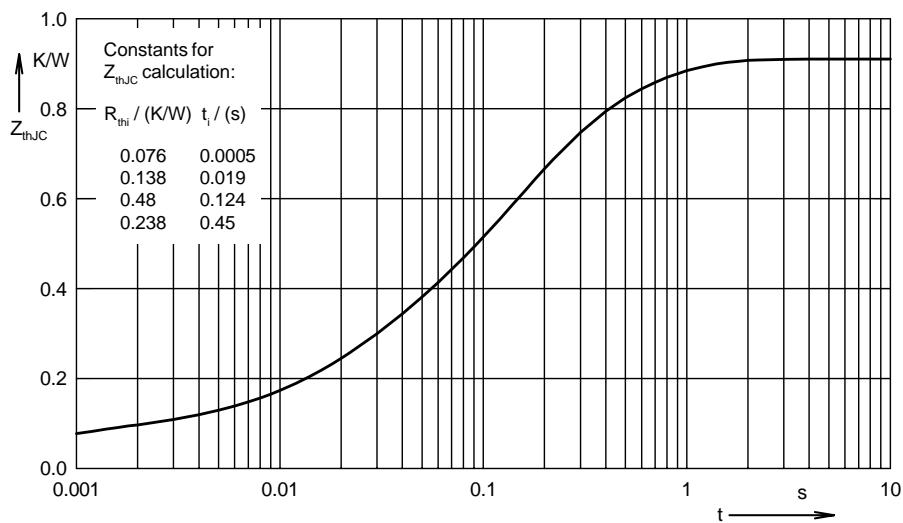


Fig. 8 Transient thermal impedance junction to case (per thyristor)

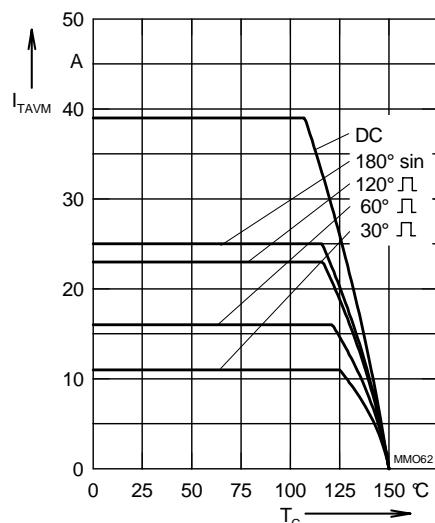


Fig. 9 Maximum forward current at case temperature